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Innovative Silicon Appoints Dr. Victor Koldyaev as Company's First Fellow

*Top Z-RAM technologist driving the next frontier in ultra-dense, single transistor
memory technology*

SANTA CLARA, Calif. – April 29, 2008 – Innovative Silicon Inc. (ISi), developer of the Z-RAM® zero-capacitor floating body memory technology, today named Dr. Victor Koldyaev an Innovative Silicon Fellow. Dr. Koldyaev is known industry-wide for his considerable technical expertise and profound impact in developing deep submicron semiconductor process technologies. This appointment acknowledges Dr. Koldyaev's contribution to advancing the Z-RAM technology, and demonstrates ISi's commitment to bringing in world-class technologists dedicated to developing the next generation in memory technology – floating body memories.

Dr. Koldyaev joined ISi in August 2007 as director of device, material science and front-end-of-the-line (FEOL) integration, where he is responsible for over-seeing process architecture development for Z-RAM memory technology across various applications. He is also a key contributor in Z-RAM device and process optimization as well as R&D of new concepts for future memory devices. Before joining ISi, Dr. Koldyaev was a Fellow at PDF Solutions (NASDAQ:PDFS), where he served as a key R&D and methodology consultant on many of the company's FEOL projects. Dr. Koldyaev has also been a principal contributor in designing and optimizing devices with FEOL integration schemes and solutions for 90nm to 32nm CMOS HP technologies, BiCMOS (also SiGe-HBT), CMOS-CCD/CIS devices and CMOS with ASIC-options for high-speed digital and analog/RF devices, Flash, eDRAM and eSRAM. Further, Dr. Koldyaev's research and development achievements have appeared in more than 100 publications, technical papers and conference proceedings, including the world's top publications in physics and applied physics. Dr. Koldyaev holds seven patents in both the U.S.A. and Russian Federation.

“Our Fellow program is used to recognize the exceptional expertise and technical contribution of our key staff,” said Mark-Eric Jones, CEO Innovative Silicon. “Victor’s extraordinary background prior to joining ISi, his technical leadership, and innovative thinking have had a significant impact in optimizing our Z-RAM technology across multiple client processes. Victor is a key contributor to bringing-up Z-RAM on sub-45nm semiconductor processes.”

About Innovative Silicon

Innovative Silicon Inc. (ISi) is the inventor and licensor of the Z-RAM® ultra-dense memory technology for stand-alone DRAM and embedded memory applications. Z-RAM is the world’s lowest-cost semiconductor memory technology – simpler to manufacture than DRAM, and a fraction the size of SRAM. ISi and the Z-RAM technology have received numerous industry awards, including the World Economic Forum’s selection of ISi as a 2008 Technology Pioneer, and by the IEEE Spectrum Magazine selection of Z-RAM as the 2007 “Emerging Technology Most Likely to Succeed.” Z-RAM is a “Zero Capacitor,” true single-transistor floating body memory that eliminates the complex capacitor found in today’s DRAM technologies – a fundamental roadblock to Moore’s Law scaling. Z-RAM provides semiconductor manufacturers with a solution to ultra-small manufacturing processes which dramatically lowers semiconductor costs. The Z-RAM memory technology has been licensed by Hynix Semiconductor for use in its DRAM chips, and by AMD for use in microprocessors. Since 2003, the company has closed three funding rounds totaling \$47 million, received over 25 patents on the technology, developed test chips in multiple technologies from 90nm to 32nm, and has established global R&D and support centers in Europe, Asia and North America. For more information see www.z-ram.com.

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